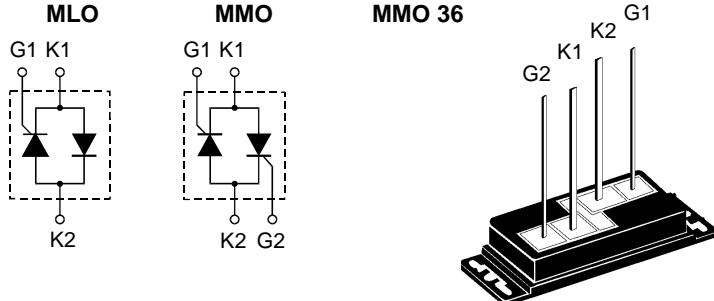


AC Controller Modules

I_{RMS} = 39 A
V_{RRM} = 1200-1600 V

V _{RSM} V _{DSM}	V _{RRM} V _{DRM}	Type
1200	1200	MLO 36-12io1
1600	1600	MMO 36-16io1



Symbol	Test Conditions	Maximum Ratings		
I _{RMS}	T _K = 85°C, 50 - 400 Hz (for single controller)	39	A	
I _{TRMS}	T _{VJ} = T _{VJM}	28	A	
I _{TAVM}	T _K = 85°C; (180° sine)	18	A	
I _{TSM}	T _{VJ} = 45°C; V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	360 390	A A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	320 350	A A
I ² t	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	645 630	A ² s A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	510 510	A ² s A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 µs V _D = 2/3 V _{DRM} I _G = 0.3 A di _G /dt = 0.3 A/µs	repetitive, I _T = 150 A non repetitive, I _T = I _{TAVM}	100 500	A/µs A/µs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GR} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/µs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 µs t _p = 300 µs	10 5	W W
P _{GAVM}			0.5	W
V _{RGM}			10	V
T _{VJ}			-40...+125	°C
T _{VJM}			125	°C
T _{stg}			-40...+125	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	3000 3600	V~ V~
M _d	Mounting torque	(M3) (UNF 4-32)	0.7 ± 0.1 6 ± 0.9	Nm lb.in.
Weight	typ.		15	g

Data according to IEC 60747 and to a single thyristor/diode unless otherwise stated.
 IXYS reserves the right to change limits, test conditions and dimensions.

Symbol	Test Conditions	Characteristic Values		
I_R, I_D	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$; $V_D = V_{DRM}$	≤	5	mA
V_T	$I_T = 45 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	≤	1.49	V
V_{TO}	For power-loss calculations only	0.85	V	
r_T		15	mΩ	
V_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤	1.0	V
I_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤	65	mA
I_{GM}	$t_p = 50 \mu\text{s}$, $f = 60 \text{ Hz}$, $I_T = I_{TAVM}$	6	A	
V_{GD}	$T_{VJ} = T_{VJM}$;	≤	0.2	V
I_{GD}	$V_D = 2/3 V_{DRM}$	≤	1	mA
I_L	$T_{VJ} = 25^\circ\text{C}$; $t_p = 10 \mu\text{s}$, $V_D = 6 \text{ V}$ $I_G = 0.3 \text{ A}$; $dI_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	150	mA
I_H	$T_{VJ} = 25^\circ\text{C}$; $V_D = 6 \text{ V}$; $R_{GK} = \infty$	≤	100	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}$; $V_D = 1/2 V_{DRM}$ $I_G = 0.3 \text{ A}$; $dI_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	2	μs
t_q	$T_{VJ} = T_{VJM}$; $I_T = 11 \text{ A}$, $t_p = 200 \mu\text{s}$; $-di/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}$; $dv/dt = 10 \text{ V}/\mu\text{s}$; $V_D = 2/3 V_{DRM}$	typ.	150	μs
R_{thJC}	per thyristor/diode; DC current	1.3	K/W	
	per module	0.65	K/W	
R_{thJK}	per thyristor/diode; DC current	1.5	K/W	
	per module	0.75	K/W	
d_s	Creeping distance on surface	6	mm	
d_A	Creepage distance in air	6	mm	
a	Max. allowable acceleration	50	m/s^2	

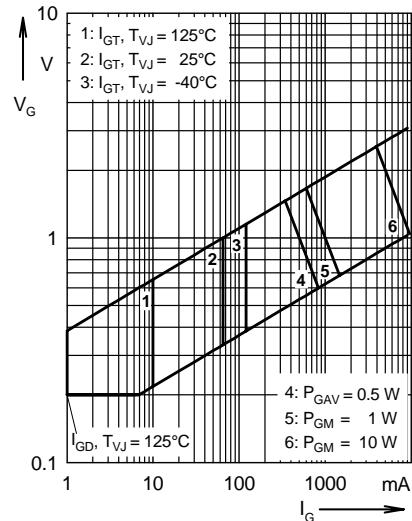


Fig. 1 Gate trigger characteristics

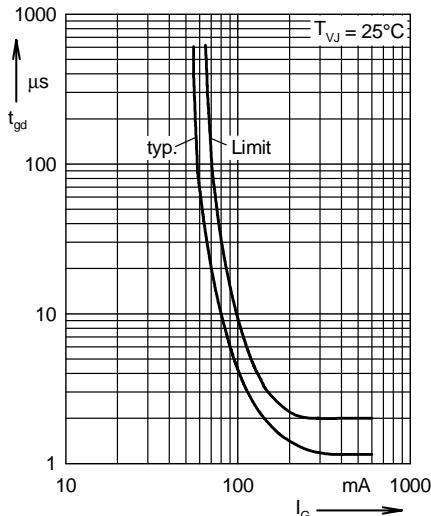


Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")
MLO 36

MMO 36

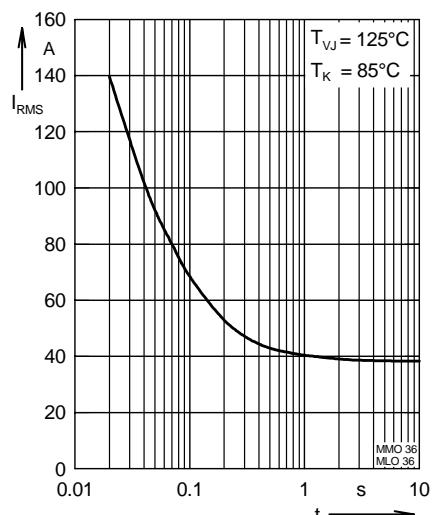
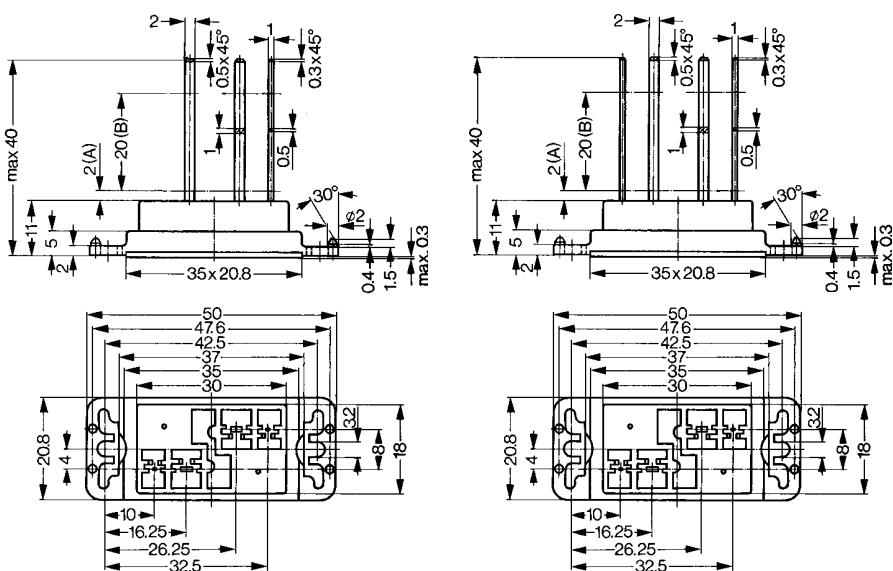


Fig. 3 Rated RMS current versus time (360° conduction)

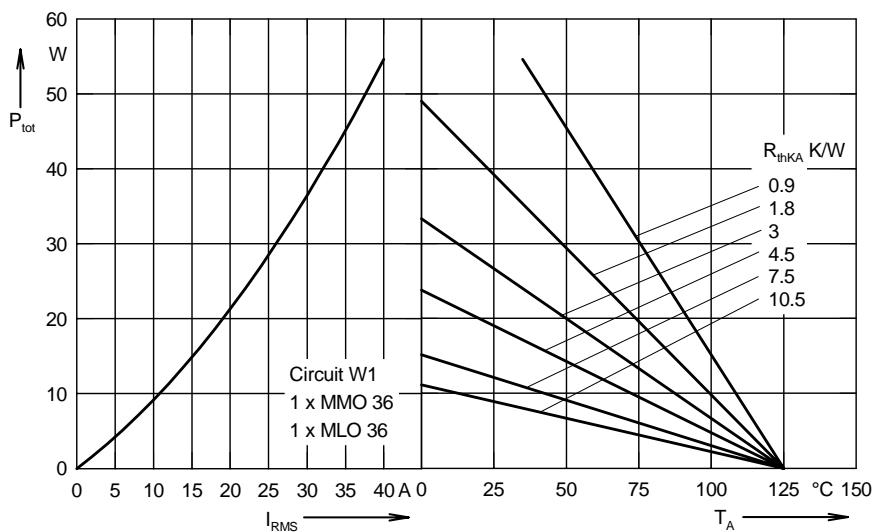


Fig. 4 Load current capability for single phase AC controller

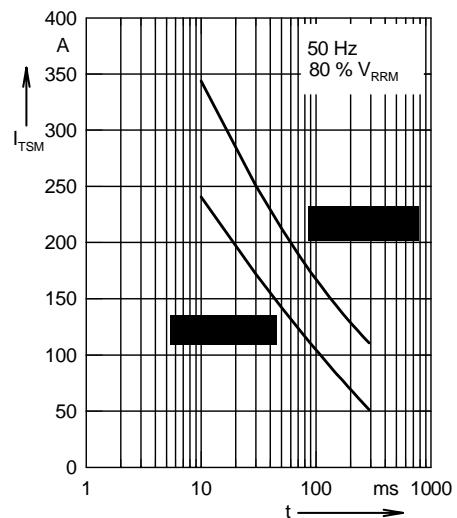


Fig. 5 Surge overload current
 I_{TSM}, I_{FSM} : Crest value, t : duration

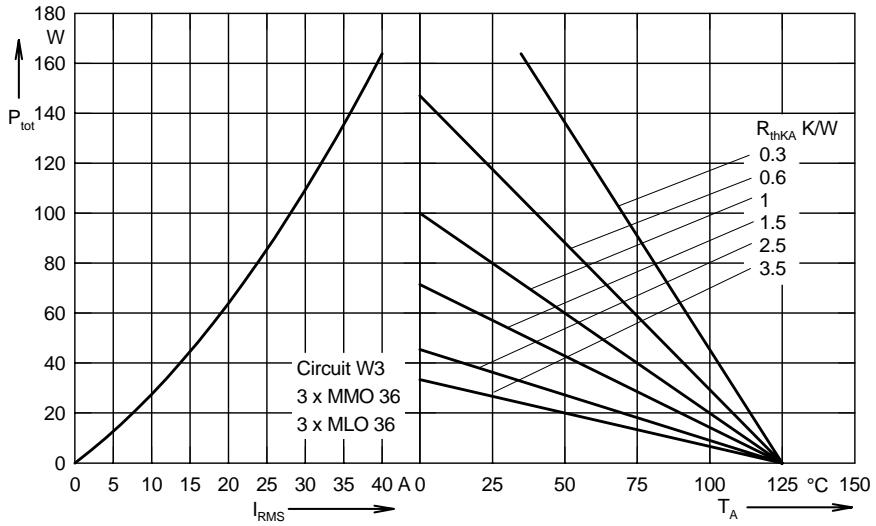


Fig. 6 Load current capability for three phase AC controller: 3xMMO 36/MLO 36

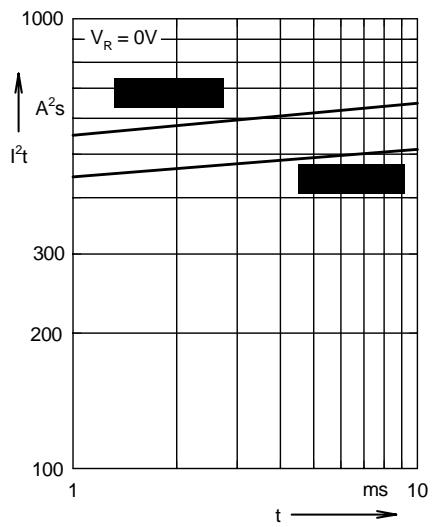


Fig. 7 I^2t versus time (1-10 ms)

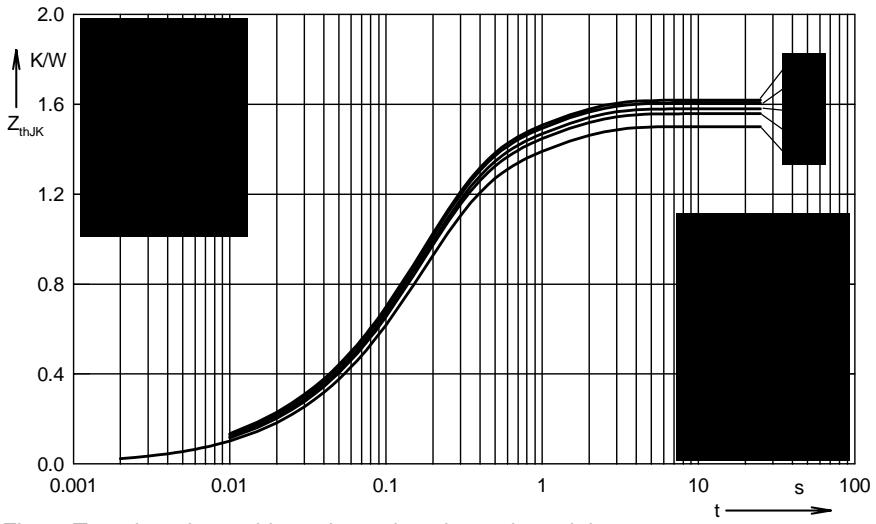


Fig. 8 Transient thermal impedance junction to heatsink (per thyristor or diode)

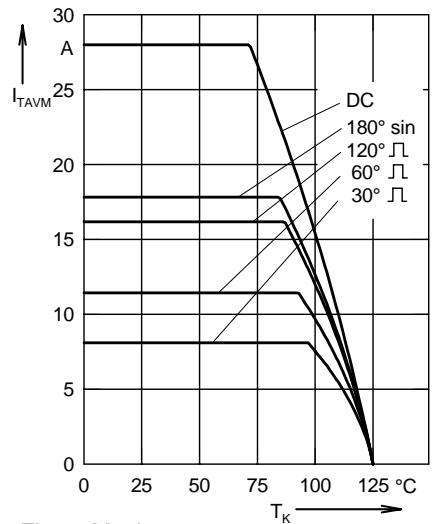


Fig. 9 Maximum on-state current versus heatsink temperature